

ABSTRACT

In a semiconductor integrated circuit device, upon connection of an interconnection made of aluminum or aluminum alloy and another interconnection made of Cu or Cu alloy, a barrier conductor film or plug is disposed at the joint portion between these interconnections. Among the interconnection layers, the uppermost one is made of a wiring material such as aluminum or aluminum alloy, while the lower, one is made of Cu or Cu alloy. The lowest interconnection is made of a conductive material other than Cu or Cu alloy. For example, the conductive material which permits minute processing and has both low resistance and high EM resistance such as tungsten is employed.